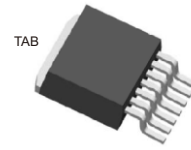


CSMD27OT080-HF

N-Channel
RoHS Device
Halogen Free



Features

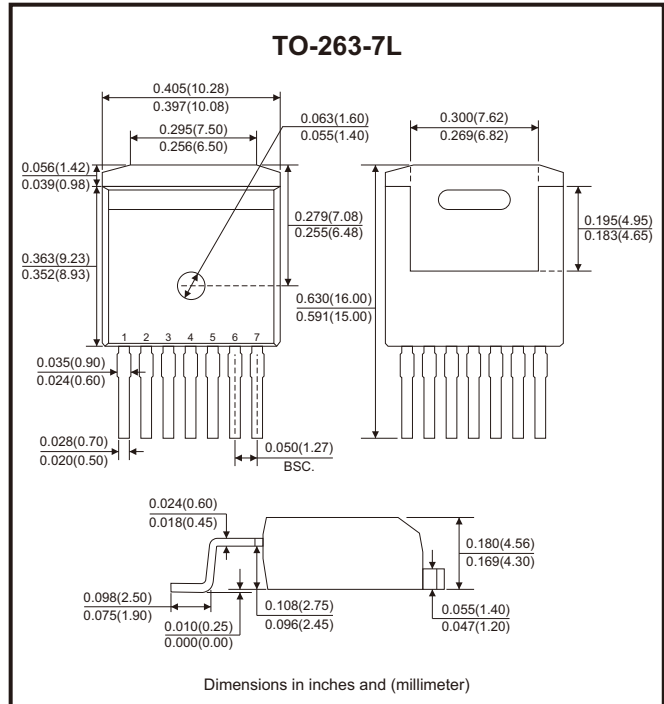
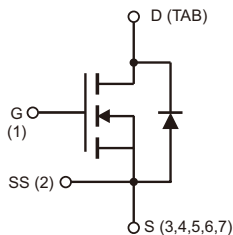
- Low on-resistance and high current density.
- Low capacitance for high frequency operation.
- Ultra high avalanche ruggedness.
- Positive temperature coefficient device.
- Low impedance kelvin source pin-out.

Mechanical data

- Case: TO-263-7L, molded plastic.
- Terminals: Solderable per MIL-STD-750, method 2026.
- Mounting position: Any.

Circuit Diagram

G: Gate
 S: Source
 D: Drain



Maximum Ratings (at T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS, max}$	1200	V
Continuous drain current	I_D	33	A
	I_D	24	
Pulse drain current	$I_{D, pulse}$	81	
Power dissipation	P_D	224	W
Recommend gate source voltage	$V_{GS, op}$	-5 to 20	V
Maximum gate source voltage	$V_{GS, max}$	-10 to 25	
Operating junction and storage temperature range	T_J, T_{STG}	-55 to 175	°C
Soldering temperature	T_L	260	
Mounting torque	M_D	1	Nm

Thermal Characteristics

Parameter	Symbol	Min	Typ	Max	Unit
Thermal resistance junction to case	$R_{\theta JC}$		0.7		°C/W

Electrical Characteristics (at $T_c=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Drain-source breakdown voltage	BV_{DSS}	$V_{GS} = 0V, I_{DS} = 100\mu A$	1200			V	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_{DS} = 20mA$	1.5	3	4.5	V	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 1200V, V_{GS} = 0V$		1	50	μA	
		$V_{DS} = 1200V, V_{GS} = 0V, T_J = 175^\circ\text{C}$		10			
Gate-source leakage current	I_{GSS}	$V_{GS} = 20V, V_{DS} = 0V$			250	nA	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 20V, I_{DS} = 15A$		80	110	m Ω	
		$V_{GS} = 20V, I_{DS} = 15A, T_J = 175^\circ\text{C}$		134			
Transconductance	g_{fs}	$V_{DS} = 9.8V, I_{DS} = 15A$		6.5		S	
Input capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 800V, f = 1MHz, V_{AC} = 25mV$		2644		pF	
Output capacitance	C_{oss}			85			
Reverse transfer capacitance	C_{rss}			8			
Effective output capacitance, energy related	$C_{o(er)}$		$V_{GS} = 0V, V_{DS} = 0 \text{ to } 800V$		202		
Effective output capacitance, time related	$C_{o(tr)}$	$I_D = \text{const.}, V_{GS} = 0V, V_{DS} = 0 \text{ to } 800V$		146			
Turn on delay time	$t_{d(on)}$	$V_{DS} = 800V, V_{GS} = -5/+20V, I_D = 20A, R_L = 40\Omega, R_{G(ext)} = 2.7\Omega$		28		ns	
Rise time	t_r			64			
Turn off delay time	$t_{d(off)}$			60			
Fall time	t_f			26.4			
Coss stored energy	E_{oss}	$V_{GS} = 0V, V_{DS} = 800V, f = 1MHz, V_{AC} = 25mV$		33		μJ	
Turn-on switching energy	E_{on}	$V_{DS} = 800V, V_{GS} = -5/+20V, I_D = 20A, R_{G(ext)} = 2.7\Omega$		148			
Turn-off switching energy	E_{off}			21.2			
Internal gate resistance	$R_{G(int.)}$	$f = 1MHz, V_{AC} = 25mV$		0.75		Ω	
Built-in SiC Diode Characteristics							
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0V, I_{SD} = 5A$		3		V	
Continuous diode forward current	I_S	$V_{GS} = 0V, T_C = 25^\circ\text{C}$		36		A	
Reverse recovery time	t_{rr}	$V_{GS} = 0V, I_{SD} = 20A, V_{DS} = 400V, di/dt = 300A/\mu s$		50		ns	
Reverse recovery charge	Q_{rr}				81		nC
Peak reverse recovery current	I_{rrm}				3.2		A

Gate Charge Characteristics (at Tc=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Value	Unit
Gate-source charge	Q_{GS}	$V_{DS} = 800V, V_{GS} = -5/+20V, I_D = 20A$	57	nC
Gate-drain charge	Q_{GD}		23	
Total gate charge	Q_G		131	
Gate plateau voltage	V_{pl}		9.9	V

Typical Rating and Characteristic Curves (CSMD27OT080-HF)

Fig.1 - Forward Output Characteristics at $T_J=25^\circ\text{C}$

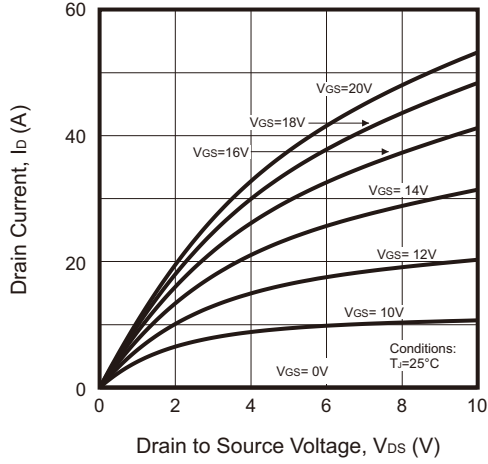


Fig.2 - Forward Output Characteristics at $T_J=175^\circ\text{C}$

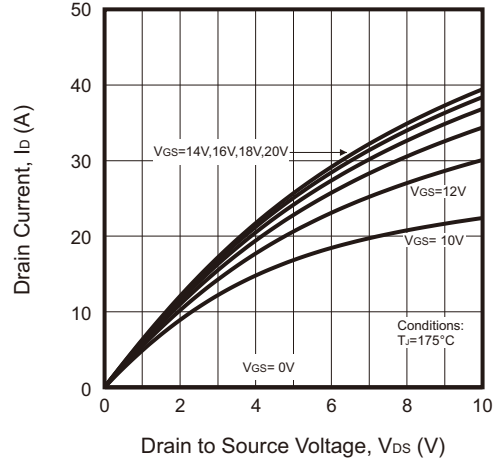


Fig.3 - On-Resistance vs. Drain Current for Various T_J

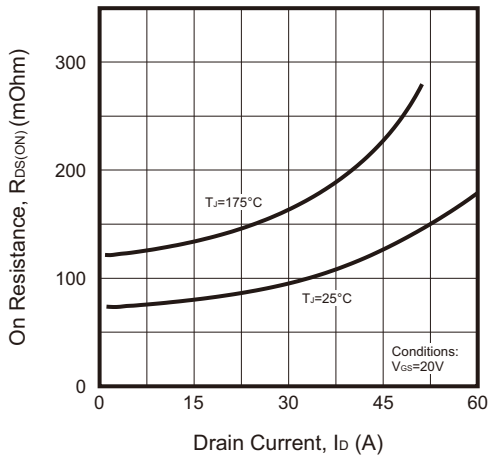


Fig.4 - Transfer Characteristics for Various T_J

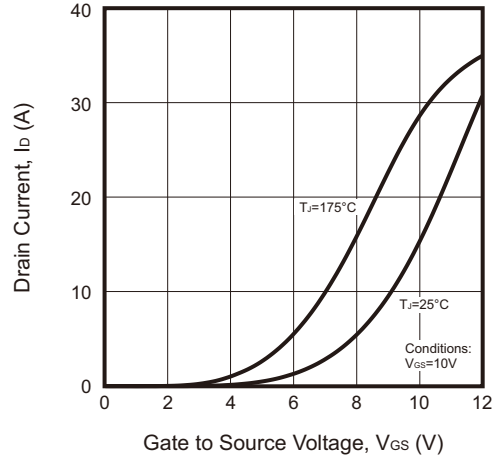


Fig.5 - On-Resistance vs. Gate Voltage for Various T_J

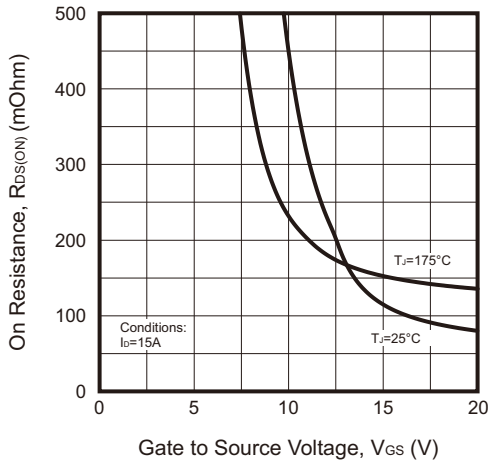
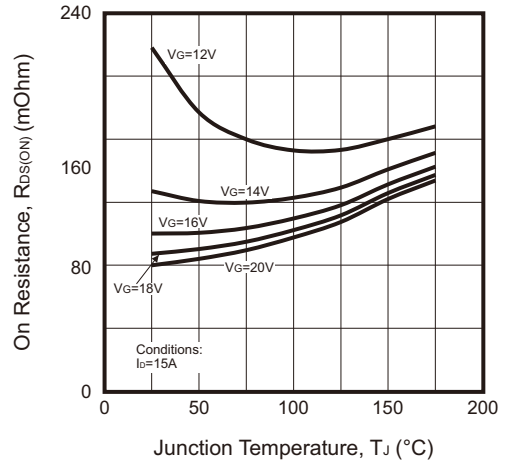


Fig.6 - On-Resistance vs. Temperature for Various Gate Voltage



Typical Rating and Characteristic Curves (CSMD27OT080-HF)

Fig.7 - Normalized On-Resistance vs. Temperature

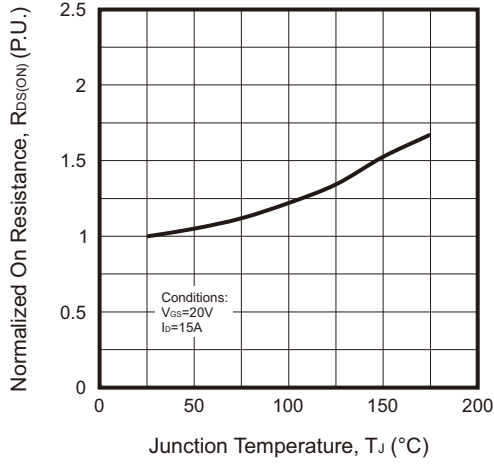


Fig.8 - Reverse Output Characteristics at $T_J=25^\circ\text{C}$

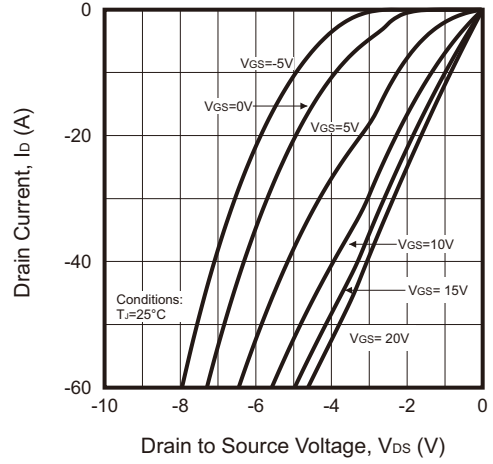


Fig.9 - Reverse Output Characteristics at $T_J=175^\circ\text{C}$

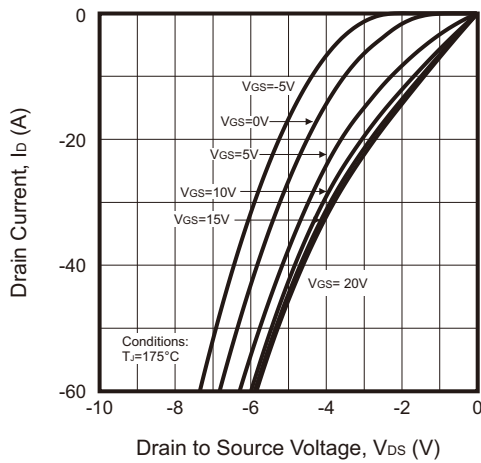


Fig.10 - Capacitance vs. Drain to Source Voltage

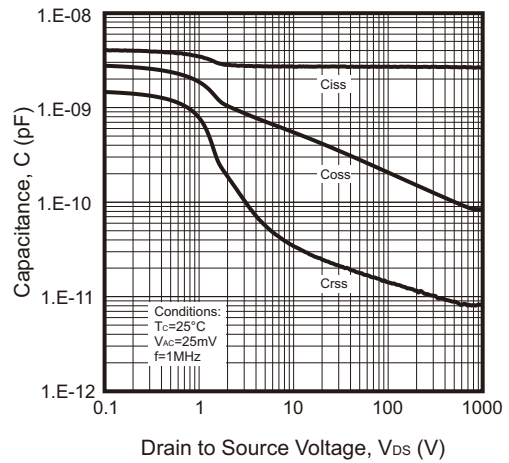


Fig.11 - Threshold Voltage vs. Temperature

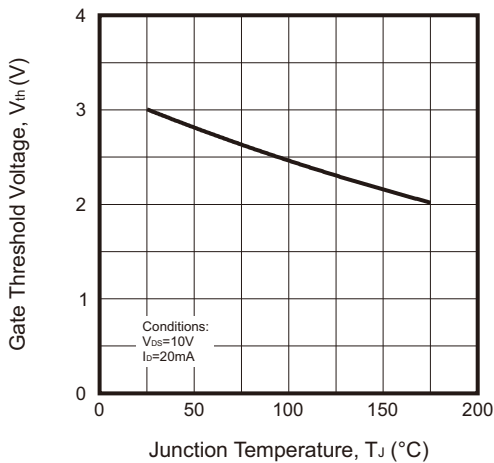
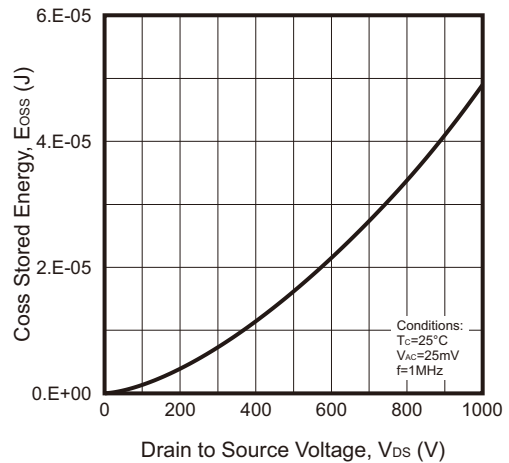


Fig.12 - Output Capacitor Stored Energy



Typical Rating and Characteristic Curves (CSMD27OT080-HF)

Fig.13 - Max. Power Dissipation Derating vs. Case Temperature

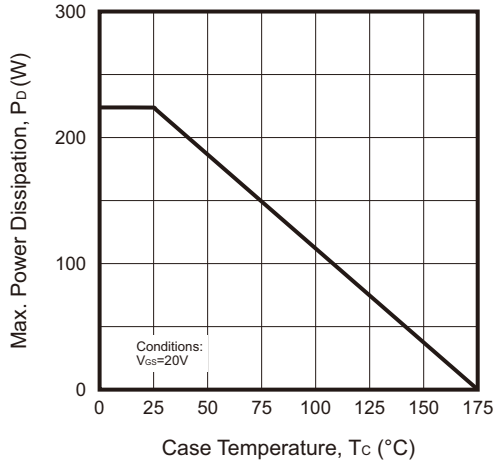


Fig.14 - Drain Current Derating vs. Case Temperature

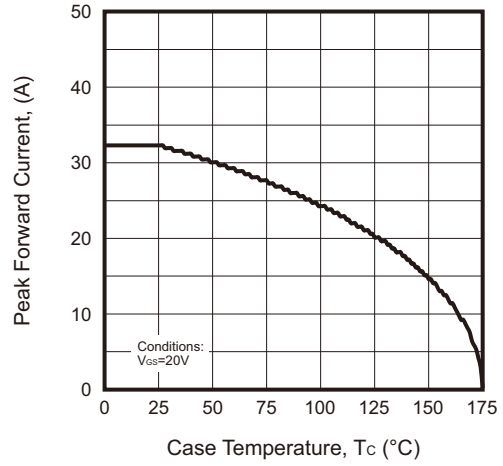


Fig.15 - Safe Operating Area

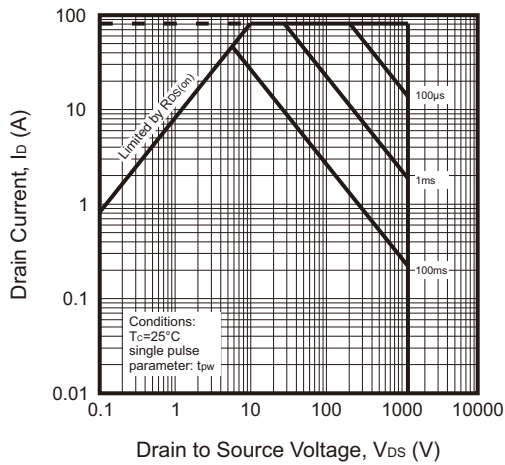


Fig.16 - Gate Charge Characteristics

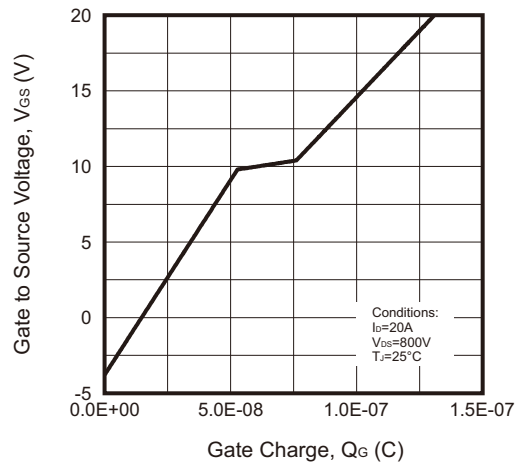


Fig.17 - Clamped Inductive Switching Energy vs. Drain Current

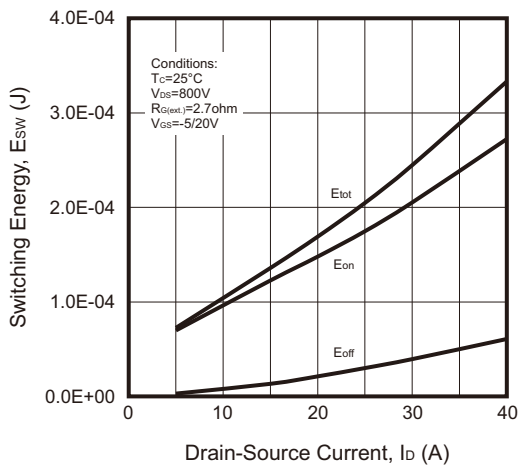
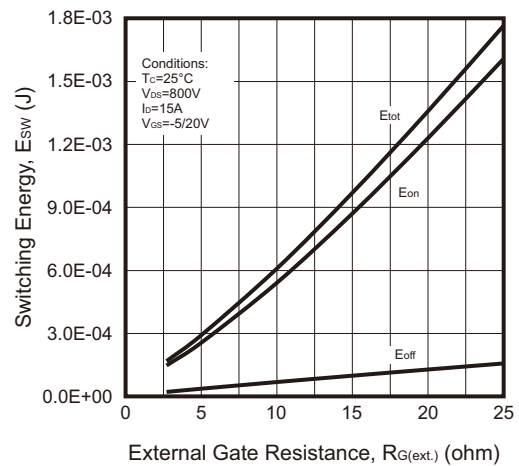
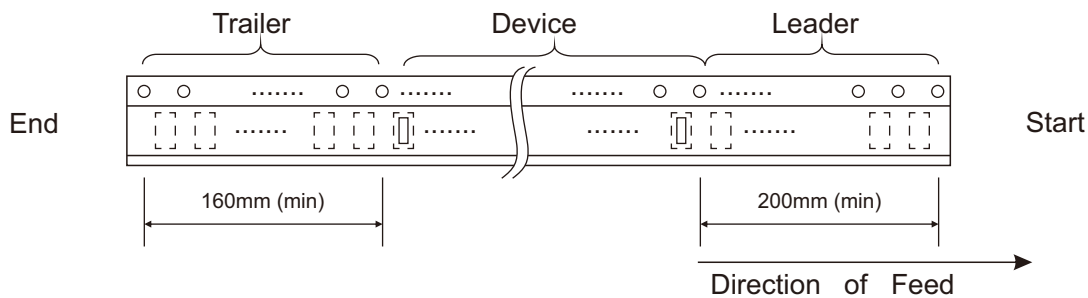
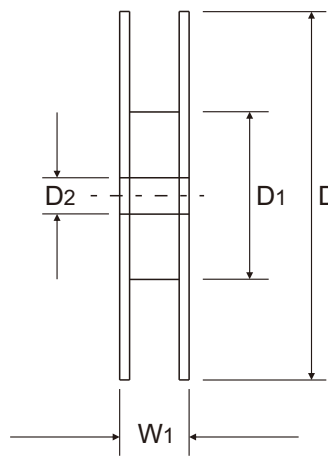
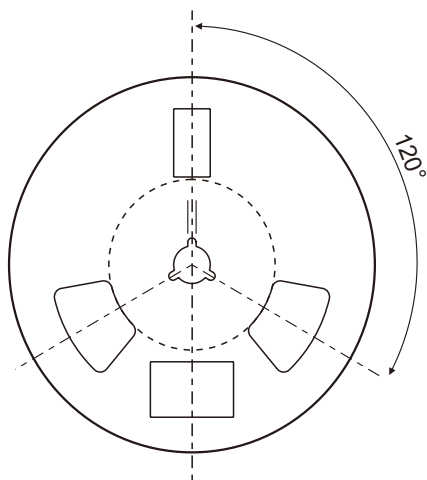
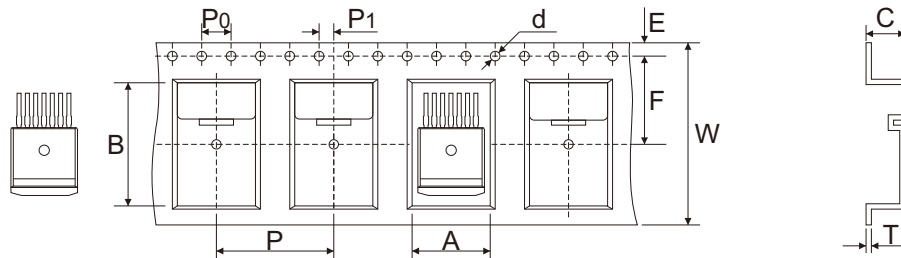


Fig.18 - Clamped Inductive Switching Energy vs. External Gate Resistor ($R_{G(ext.)}$)



Reel Taping Specification

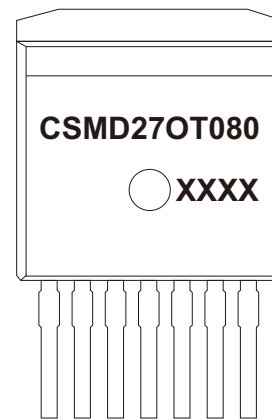


TO-263 -7L	SYMBOL	A	B	C	d	D	D ₁	D ₂
	(mm)	10.80 ± 0.10	16.30 ± 0.10	5.26 ± 0.10	1.55 ± 0.05	330.00 ± 2.00	100.00 ± 0.50	13.00 + 0.50 - 0.20
	(inch)	0.425 ± 0.004	0.642 ± 0.004	0.207 ± 0.004	0.061 ± 0.002	12.992 ± 0.079	3.937 ± 0.020	0.512 + 0.020 - 0.008

TO-263 -7L	SYMBOL	E	F	P	P ₀	P ₁	T	W	W ₁
	(mm)	1.75 ± 0.10	11.50 ± 0.10	16.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	0.35 ± 0.05	24.00 ± 0.30	30.40 Max
	(inch)	0.069 ± 0.004	0.453 ± 0.004	0.630 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.014 ± 0.002	0.945 ± 0.012	1.197 Max

Marking Code

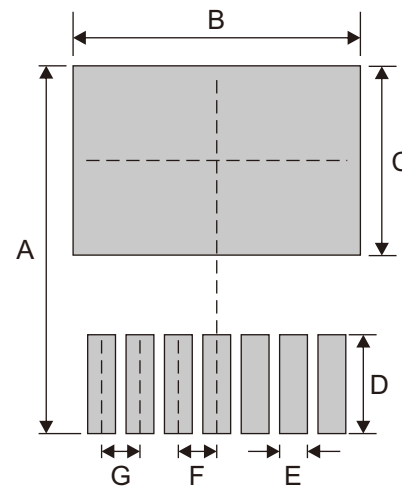
Part Number	Marking Code
CSMD27OT080-HF	CSMD27OT080



XXXX = Control code

Suggested P.C.B. PAD Layout

SIZE	TO-263-7L	
	(mm)	(inch)
A	16.30	0.642
B	11.00	0.433
C	8.40	0.331
D	3.40	0.134
E	0.90	0.035
F	1.27	0.050
G	1.27	0.050



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
TO-263-7L	800	13